ABSTRACT

ABRASIVE COMPOSITION FOR POLISHING A METAL LAYER ON A SEMICONDUCTOR SUBSTRATE, AND USE OF THE SAME

An abrasive composition for polishing a metal layer on a semiconductor substrate is provided comprising an oxidizing agent, abrasive particles which comprise cerium oxide, and optionally abrasive particles which comprise at least one oxide selected from (a) metal oxides other than cerium oxide and (b) silicon oxide, the abrasive particles having a mean particle size of 3 μm or less. A method for polishing and planarizing a metal layer formed on a semiconductor substrate, a method of increasing evenness of the surface of a metal layer on a semiconductor substrate and a process for polishing the surface of a metal layer on a semiconductor substrate to prevent the occurrence of wire breaking using the abrasive composition are also provided.

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